

Silicon NPN Power Transistors

BU931T

DESCRIPTION

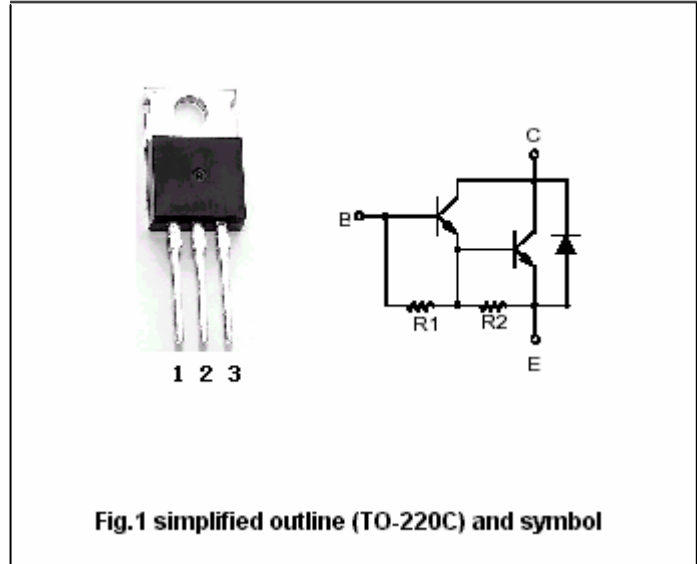
- With TO-220C package
- Fast switching speed
- DARLINGTON

APPLICATIONS

- High ruggedness electronic ignitions..
- High voltage ignition coil driver

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	500	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		10	A
I _{CM}	Collector current (peak)		15	A
I _B	Base current		1	A
I _{BM}	Base current		5	A
P _{tot}	Total power dissipation	T _C =25℃	125	W
T _j	Max.operating junction temperature		175	℃
T _{stg}	Storage temperature		-65~175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-case}	Thermal resistance junction case	1.2	℃/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.1 A ; I _B =0; L=10mH	400			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =7A ; I _B =0.07A			1.6	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =8A; I _B =0.1 A			1.8	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =7A ; I _B =0.07A			2.2	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =8A; I _B =0.1 A			2.4	V
I _{CES}	Collector cut-off current	V _{CE} =500V; V _{BE} =0; T _j =125 °C			10 500	μA
I _{CEO}	Collector cut-off current	V _{CE} =450V; I _B =0; T _j =125 °C			0.1 0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			20	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =10V	300			
V _F	Diode forward voltage	I _F =10A			2.5	V

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PACKAGE OUTLINE

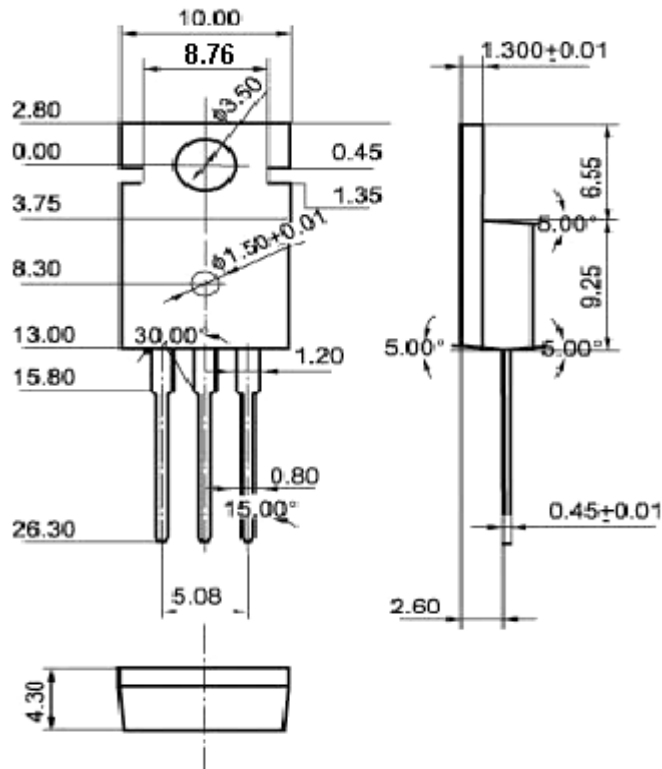


Fig.2 Outline dimensions (unindicated tolerance: 0.1mm)